NSN 5961-00-238-6889

Semiconductor Device Set - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-238-6889 **Inclosure Material:** Metal all transistor **Overall Length:** 0.210 inches all transistor **Terminal Length:** 0.500 inches all transistor **Overall Diameter:** 0.209 inches all transistor and 0.230 inches all transistor **Internal Configuration:** Field effect all transistor **Channel Polarity And Control Type (non-core):** P-channel junction type 2nd transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Terminal all transistor **Terminal Circle Diameter:** 0.100 inches all transistor **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 50.0 drain to gate voltage 1st transistor and 50.0 forward gate to source voltage 1st transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current minor all transistor **Power Rating Per Characteristic:** 300.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 4 uninsulated wire lead all transistor Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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